

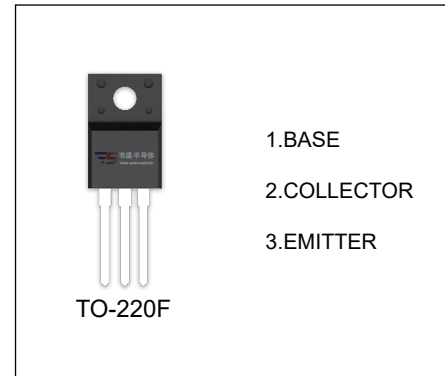
## KTB1367 TRANSISTOR (PNP)

### FEATURES

- Low Collector-Emitter Saturation Voltage
- General Purpose Applications

### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-100	V
$V_{CEO}$	Collector-Emitter Voltage	-100	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-5	A
$P_C$	Collector Power Dissipation	2	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	62.5	$^{\circ}\text{C}/\text{W}$
$T_J, T_{stg}$	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$



### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=-50\text{mA}, I_B=0$	-100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}^*$	$I_E=-10\text{mA}, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-100\text{V}, I_E=0$			-100	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE}=-50\text{V}, I_B=0$			-500	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5\text{V}, I_C=0$			-1	mA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5\text{V}, I_C=-1\text{A}$	40		240	
	$h_{FE(2)}$	$V_{CE}=-5\text{V}, I_C=-4\text{A}$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-4\text{A}, I_B=-0.4\text{A}$			-2	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=-5\text{V}, I_C=-4\text{A}$			-1.5	V
Collector output capacitance	$C_{ob}$	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		270		pF
Transition frequency	$f_T$	$V_{CE}=-5\text{V}, I_C=-1\text{A}$		5		MHz

\*Pulse test

### CLASSIFICATION OF $h_{FE(1)}$

RANK	R	O	Y
RANGE	40-80	70-140	120-240